

DOCKET NO. SC12858TP

Please amend the subject application as follows:

**IN THE SPECIFICATION:**

On page 1, lines 1 and 2, amend the title as follows:

**METHOD FOR FORMING A NON-VOLATILE MEMORY HAVING A REFERENCE**  
**TRANSISTOR AND METHOD FOR FORMING**

On page 1, lines 5-10, amend the related application paragraph as follows:

**RELATED APPLICATION**

This application is related to United States patent application ~~attorney docket number~~  
~~SC12996TC~~ Serial No. 10/609,359, entitled "Variable Gate Bias For A Reference Transistor In  
A Non-Volatile Memory" filed concurrently herewith by Chindalore et al., and assigned to the  
assignee hereof.

On page 2, lines 1 and 2, amend the title as follows:

**METHOD FOR FORMING A NON-VOLATILE MEMORY HAVING A REFERENCE**  
**TRANSISTOR AND METHOD FOR FORMING**